

No.3792

2SC4437

NPN Triple Diffused Planar Silicon Transistor

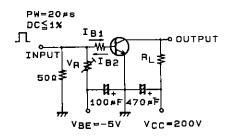
Ultrahigh-Definition Color Display Horizontal Deflection Output Applications

## **Features**

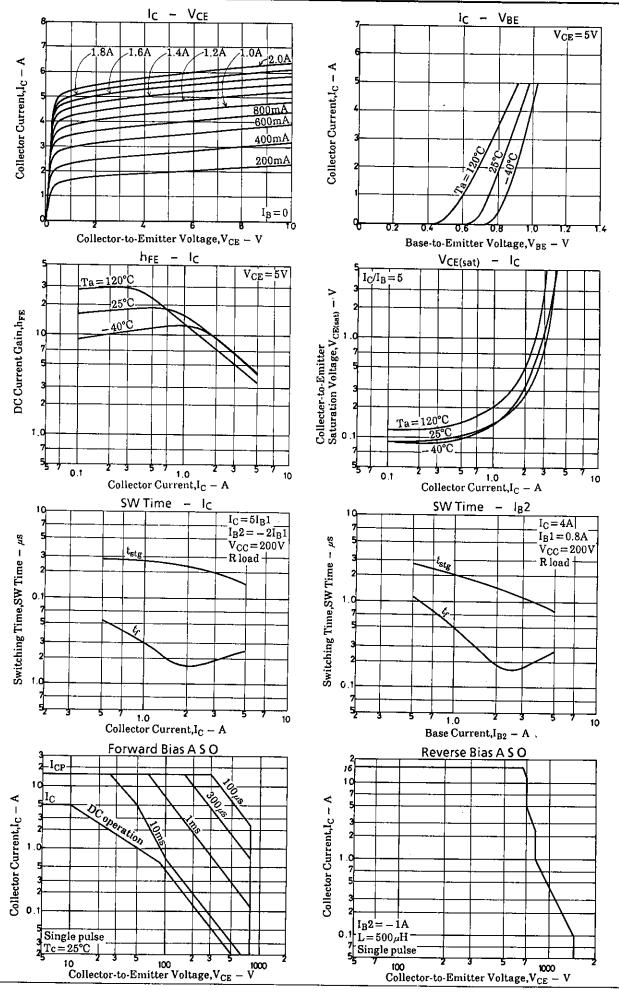
- · High speed ( $t_f = 0.3$ ns max).
- High breakdown voltage ( $V_{CBO} = 1500V$ ).
- · High reliability (Adoption of HVP process).
- · Adoption of MBIT process.

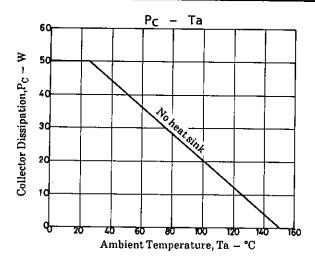
Absolute Maximum Ratings at Ta = 25°C					unit	
Collector-to-Base Voltage	$V_{CBO}$		1500		v	
Collector-to-Emitter Voltage	$V_{CEO}$			800	v	
Emitter-to-Base Voltage	$V_{EBO}$			7	v	
Collector Current	$I_{\mathbf{C}}$			5	Α	
Collector Current (Pulse)	$I_{CP}$	·		16	Α	
Collector Dissipation	$P_{\mathbf{C}}$			3	W	
_	-	$Tc = 25^{\circ}C$		50	W	
Junction Temperature	Tj			150	°C	
Storage Temperature	Tstg		-55  to  +150		°C	
Electrical Characteristics at Ta = 25°C			min	typ	max	unit
Collector Cutoff Current	$I_{CES}$	$V_{CE} = 1500V$		٧.	1.0	mA
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 800 V_{IE} = 0$			10	$\mu$ A
Collector Sustain Voltage	$V_{CEO(sus)}$	$I_{\rm C} = 100  \text{mA}, I_{\rm B} = 0$	800			'v
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 4V, I_C = 0$			1	mΑ
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 4A, I_B = 1A$			5	V
<b>B-E Saturation Voltage</b>	$V_{BE(sat)}$	$I_C = 4A, I_B = 1A$			1.5	V
DC Current Gain	$h_{FE}(1)$	$V_{CE} = 5V, I_{C} = 1A$	8			
	$h_{FE}(2)$	$V_{CE} = 5V, I_{C} = 4A$	4		6	
Storage Time	$t_{stg}$	$I_C = 4A, I_{B1} = 0.8A, I_{B2} = -1.6A$			3.0	μS
Fall Time	$t_f$	$I_C = 4A, I_{B1} = 0.8A, I_{B2} = -1.6A$			0.3	μs

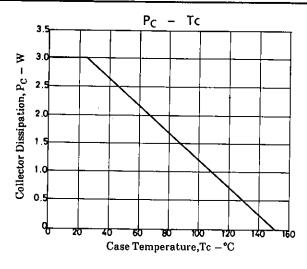
## Switching Time Test Circuit



## Package Dimensions 2039B (unit: mm)







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